

FEATURES

- Red Enhanced
- Low Noise
- High Response
- High Shunt Resistance
- Low Profile TO-5 Package

Electro-Optical Characteristics at 25°C

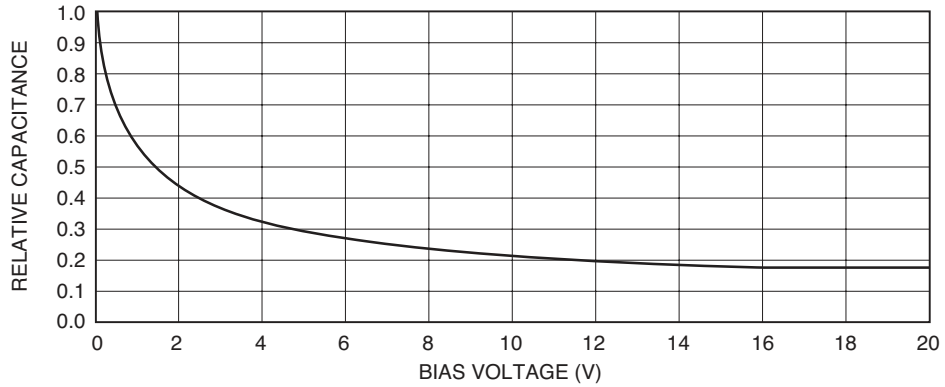
Characteristic	Test Conditions	Min	Typ	Max	Units
Dark Current, I _D	V _R = 5 V		0.9	5	na
Shunt Resistance, R _{SH}	V _R = 10 mV		300		MΩ
Junction Capacitance, C _J	V _R = 0 V, f = 1 MHz		30		pF
Junction Capacitance, C _J	V _R = 10 V, f = 1 MHz		7.5		pF
Spectral Application Range, λ _{range}	Spot Scan	250		1100	nm
Responsivity, R	λ = 633 nm, V _R = 0 V	0.32	0.36		A/W
Responsivity, R	λ = 900 nm, V _R = 0 V	0.5	0.6		A/W
Breakdown Voltage, V _R	I _R = 10 μA	25	60		V
Noise Equivalent Power, NEP	V _R = 0 V, λ = 950 nm		2.5 x 10 ⁻¹⁴		W/√HZ
Response Time, t _r ¹	RL = 50 Ω, V _R = 0 V		190		nsec
Response Time, t _r ¹	RL = 50 Ω, V _R = 10 V		8		nsec

¹ Response time of 10% to 90% is specified at 660 nm.

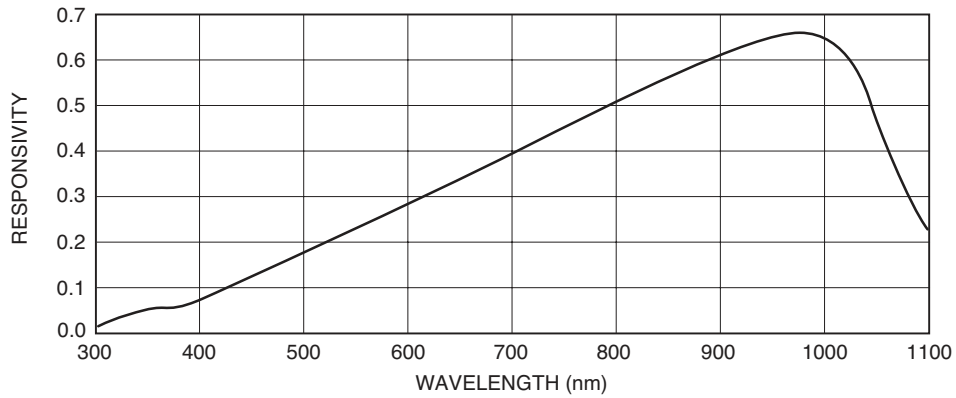
Absolute Maximum Ratings at 25°C

Parameter	Min	Max	Units
Reverse Voltage, V _R		100	V
Storage Temperature, T _{STG}	-55	+150	°C
Operating Temperature, T _O	-40	+125	°C
Lead Soldering Temperature (1/16" from case for 3 sec)		+260	°C

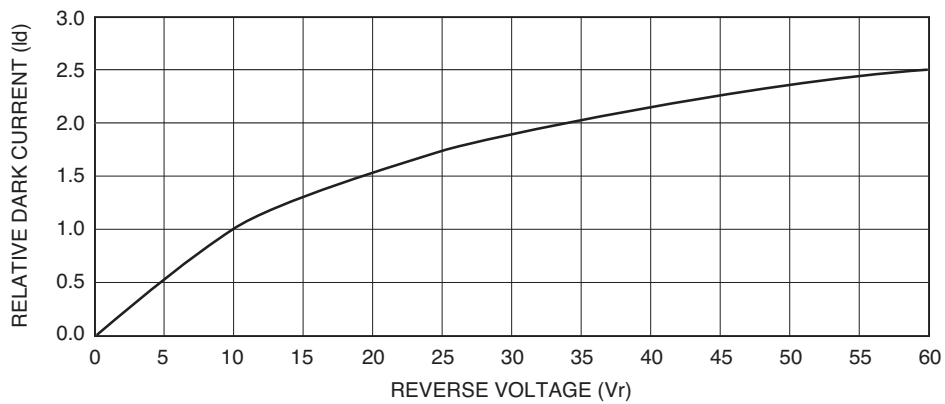
Capacitance vs Bias Voltage



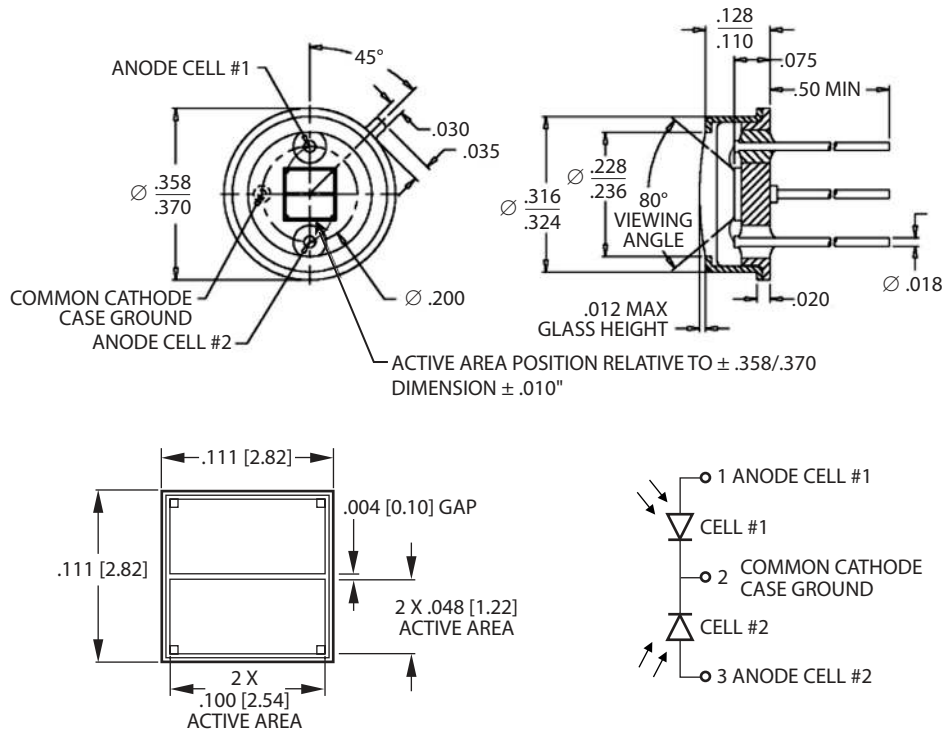
Typical Spectral Response



Dark Current vs Voltage



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.